

- 11/1/2011
- (a) depositing a first film of p-type copper indium diselenide film on a metal back contact
- (b) depositing on the upper surface of the copper indium diselenide film a group IIb halide [(a,b) and VII elemental salt];
- (c) [converting] doping the p-type [the] upper copper indium diselenide film surface n-type by thermal diffusion of the [salt] group IIb halide into the copper indium diselenide film surface and cleaning the n-type surface;
- (d) depositing a second thin film layer of high resistivity zinc oxide; and
- (e) depositing a third film of n-type transparent zinc oxide on the second thin film high resistivity zinc oxide layer.

Please amend claim 2, as follows:

2. (once amended) A process according to claim [1 in which] 1 wherein the group IIb halide [(a,b) and VII elemental salt] is zinc chloride.

Please rewrite claims 6 and 7, as follows:

Claim 6, line 20, delete "elemental salt" and substitute therefor --group IIb halide--

Claim 7, line 22, delete "elemental salt" and substitute therefor --group IIb halide--

Please amend claims 8, 10, and 11, as follows: